

DOCKET NO.: 220110US2S



IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :

AKIRA HOKAZONO

: EXAMINER: DICKEY, T. L.

SERIAL NO: 10/083,163 :

FILED: FEBRUARY 27, 2002

: GROUP ART UNIT: 2826

FOR: SEMICONDUCTOR DEVICE
HAVING ACTIVE REGIONS
CONNECTED TOGETHER BY
INTERCONNECT LAYER AND
METHOD OF MANUFACTURE
THEREOF

AMENDMENT

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

In response to the Office Action of March 19, 2003, please amend the above-identified application as follows:

IN THE SPECIFICATION

Please amend the specification as indicated below.¹

Please amend the paragraph on page 2, lines 8-15, as follows:

A' SRAMs (Static Random Access Memories) contain interconnect patterns, called local interconnects, for interconnection of sources, gate electrodes and drains of MOS transistors. The method of forming the local interconnects involves forming a large opening in an interlayer dielectric film above the sources, gate electrodes and drains and filling the opening with a conductive material.

¹A marked-up copy of the amendments is attached hereto.

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